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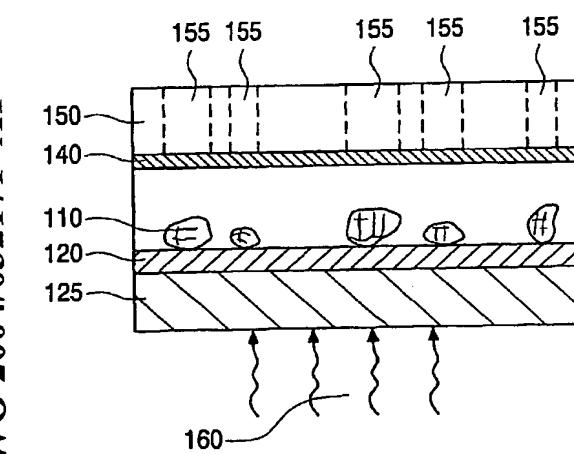
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(54) Title: FIELD EMISSION DEVICE WITH SELF-ALIGNED GATE ELECTRODE STRUCTURE, AND METHOD OF MANUFACTURING SAME



(57) Abstract: The invention relates to a field emission device, and a method of manufacturing same. The field emission device comprises a gate electrode (140, 340, 440) which is provided with a pattern of electron passing apertures (135, 335, 435). The gate electrode (140, 340, 440) is arranged near particles (110, 310, 410) distributed on a substrate (125, 325, 425), at least a part of said particles (110, 310, 410) being arranged for emitting electrons. By means of the gate electrode (140, 340, 440), an electric field is applicable by means of which emitting particles emit electrons. Particularly good electron emission is obtained, because the pattern of apertures (135, 335, 435) is similar to the distribution of particles (110, 310, 410) on the substrate. This is achieved by means of the manufacturing method, in which the particles (110, 310, 410) are used in an illumination step to mask regions (155, 355) of a photo layer (150, 352). Thus, a pattern is obtained in the photo layer (150, 352), which can be used to obtain a similar pattern in the gate electrode (140, 340, 440) with relative ease.

WO 2004/032171 A1



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